Silicon N Channel MOS Type / Silicon Epitaxial Schottky Barrier Diode

SSM5H06FE

DC-DC Converter

- Combined Nch MOSFET and Schottky Diode in one Package.
- Small package

Maximum Ratings (Ta = 25°C) MOSFET

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	20	V
Gate-Source voltage		V_{GSS}	±10	V
Drain current	DC	I_D	100	mA
	Pulse	I_{DP} (Note 2)	200	
Drain power dissipation		P_D (Note 1)	150	mW
Channel temperature		T_{ch}	150	°C

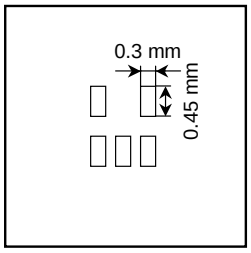
Maximum Ratings (Ta = 25°C) SCHOTTKY DIODE

Characteristics	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	15	V
Reverse voltage	V_R	12	V
Average forward current	I_O	100	mA
Peak one cycle surge forward current (non-repetitive)	I_{FSM}	1 (50 Hz)	A
Junction temperature	T_j	125	°C

Maximum Ratings (Ta = 25°C) MOSFET, DIODE COMMON

Characteristics	Symbol	Rating	Unit
Storage temperature	T_{stg}	−55~125	°C
Operating temperature	T_{opr} (Note 3)	−40~100	°C

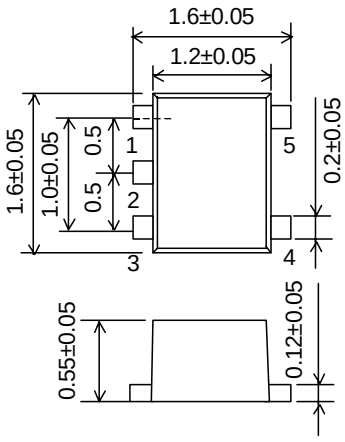
Note 1: Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.135 mm^2 × 5)



Note 2: The pulse width limited by max channel temperature.

Note 3: Operating temperature limited by max channel temperature and max junction temperature.

Unit: mm



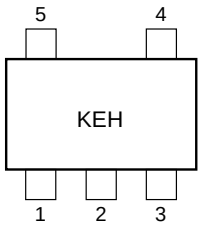
1.Gate 4.Cathode
2.Source 5.Drain
3.Anode

ESV

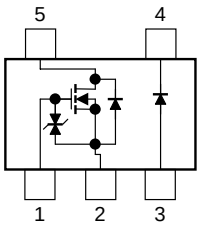
JEDEC	—
JEITA	—
TOSHIBA	2-2P1C

Weight: 3 mg (typ.)

Marking



Equivalent Circuit



Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

The Channel-to-Ambient thermal resistance $R_{th\ (ch\text{-}a)}$ and the drain power dissipation P_D vary according to the board material, board area, board thickness and pad area. When using this device, please take heat dissipation fully into account.

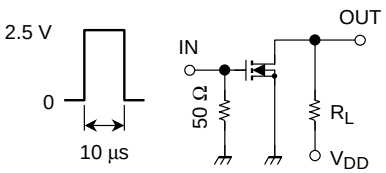
MOSFET

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0	—	—	±1	μA
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 0.1 mA, V_{GS} = 0	20	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 0.1 mA	0.6	—	1.1	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 10 mA	40	—	—	mS
Drain-Source on-resistance		$R_{DS\ (ON)}$	I_D = 10 mA, V_{GS} = 4 V	—	1.5	3.0	Ω
			I_D = 10 mA, V_{GS} = 2.5 V	—	2.2	4.0	
			I_D = 1 mA, V_{GS} = 1.5 V	—	5.2	15	
Input capacitance		C_{iss}	V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz	—	9.3	—	pF
Reverse transfer capacitance		C_{rss}	V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz	—	4.5	—	pF
Output capacitance		C_{oss}	V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz	—	9.8	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = 3 V, I_D = 10 mA, V_{GS} = 0~2.5 V	—	70	—	ns
	Turn-off time	t_{off}		—	125	—	

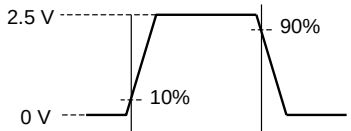
Switching Time Test Circuit

(a) Test circuit

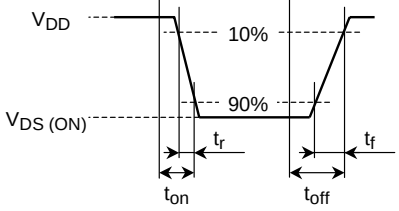


V_{DD} = 3 V
Duty ≦ 1%
V_{IN}: t_r, t_f < 5 ns
(Z_{out} = 50 Ω)
Common Source
Ta = 25°C

(b) V_{IN}



(c) V_{OUT}



Precaution

V_{th} can be expressed as voltage between gate and source when the low operating current value is I_D 100 μA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th} and $V_{GS\ (off)}$ requires a lower voltage than V_{th}.

(The relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$)

Please take this into consideration when using the device. The V_{GS} recommended voltage for turning on this product is 1.8 V or higher.

Schottky Diode

Electrical Characteristics (Ta = 25°C)

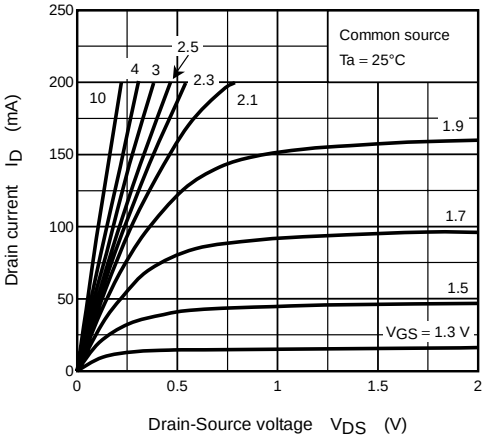
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F\ (1)}$	I_F = 1mA	—	0.18	—	V
	$V_{F\ (2)}$	I_F = 5mA	—	0.23	0.30	V
	$V_{F\ (3)}$	I_F = 100mA	—	0.35	0.50	V
Reverse current	I_R	V_R = 12 V	—	—	22	μA
Total capacitance	C_T	V_R = 0 V, f = 1 MHz	—	20	40	pF

Precaution

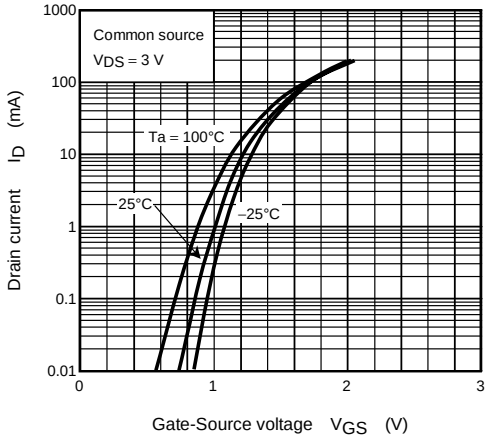
The schottky barrier diodes of this product have large-reverse-current-leakage characteristics compared to other switching diodes. This current leakage and improper operating temperature or voltage may cause thermal runaway resulting in breakdown. Take forward and reverse loss into consideration in radiation design and safety design.

MOSFET Electrical Characteristics Graph

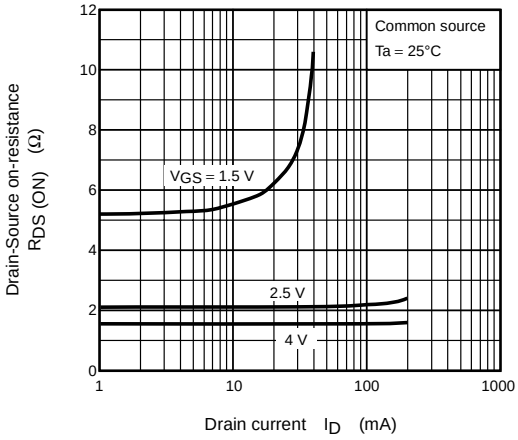
$I_D - V_{DS}$



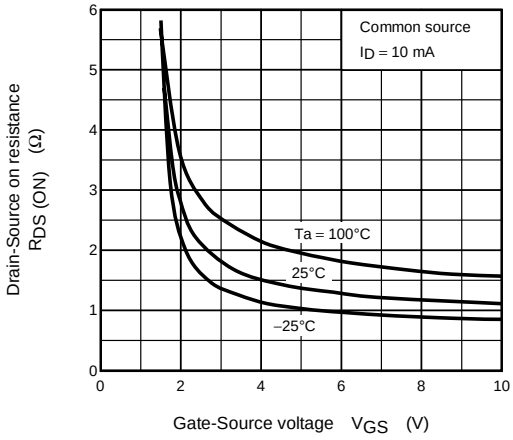
$I_D - V_{GS}$



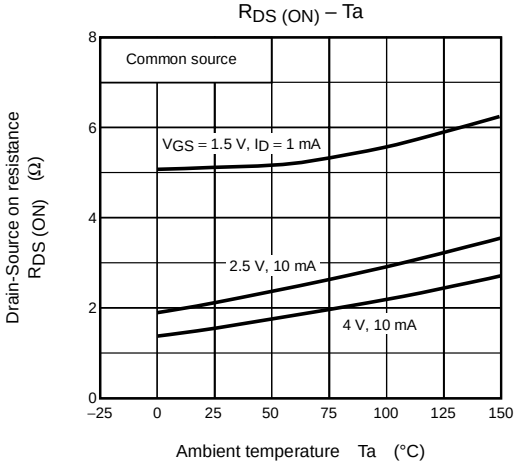
$R_{DS\ (ON)} - I_D$



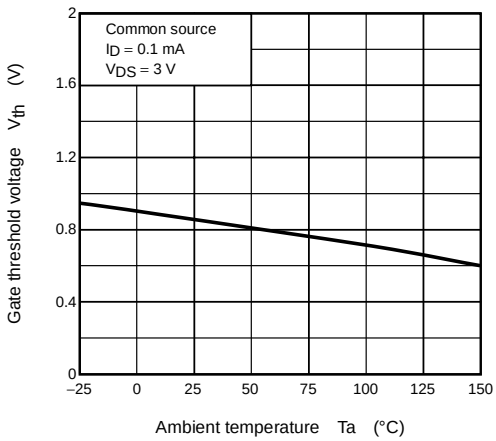
$R_{DS\ (ON)} - V_{GS}$



$R_{DS\ (ON)} - Ta$

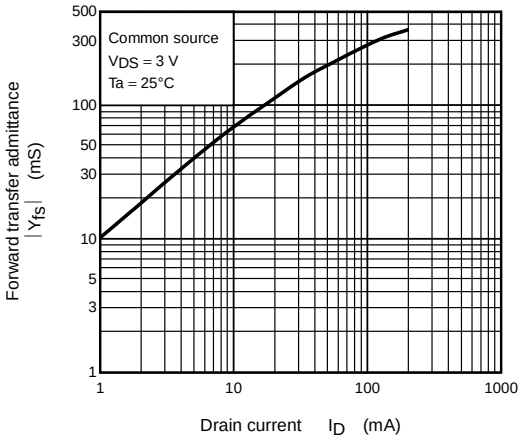


$V_{th} - Ta$

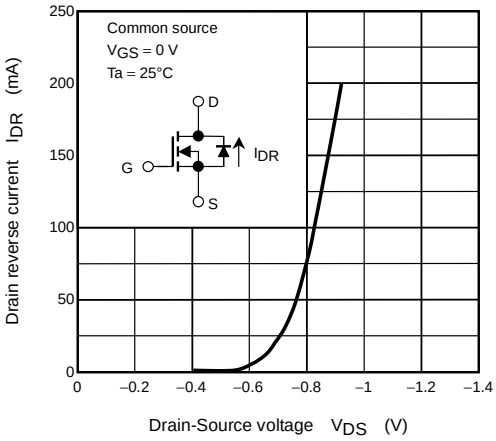


MOSFET Electrical Characteristics Graph

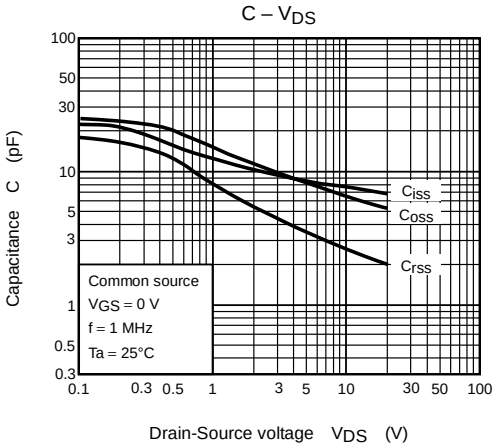
$|Y_{fs}| - I_D$



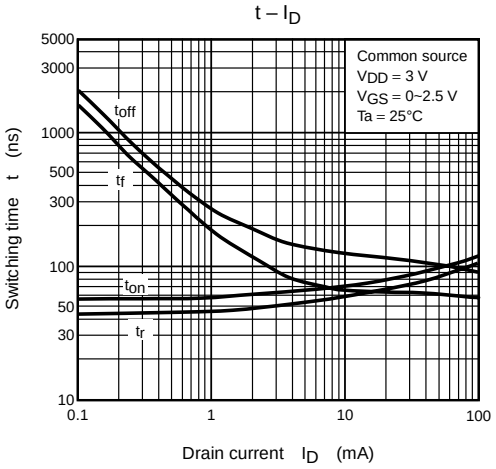
$I_{DR} - V_{DS}$



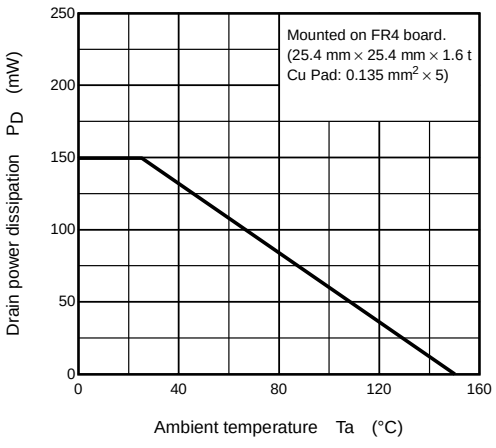
$C - V_{DS}$



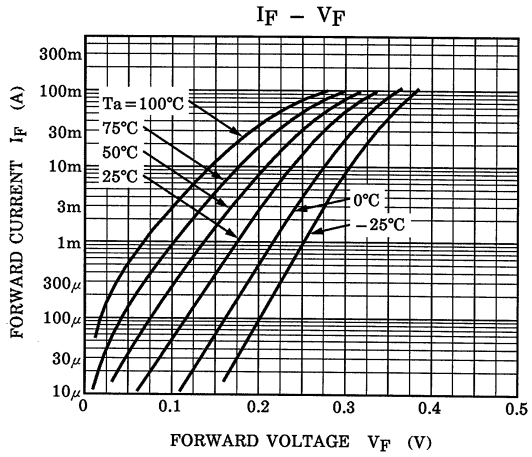
$t - I_D$

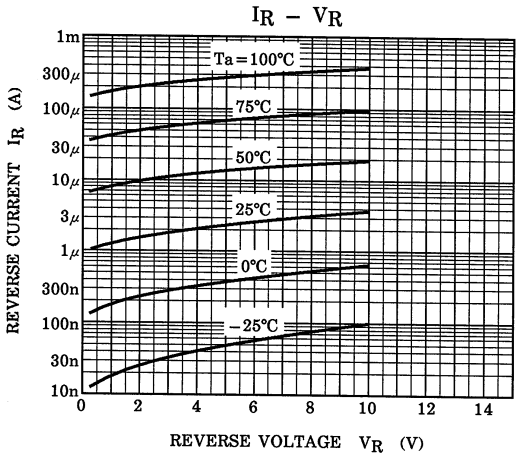


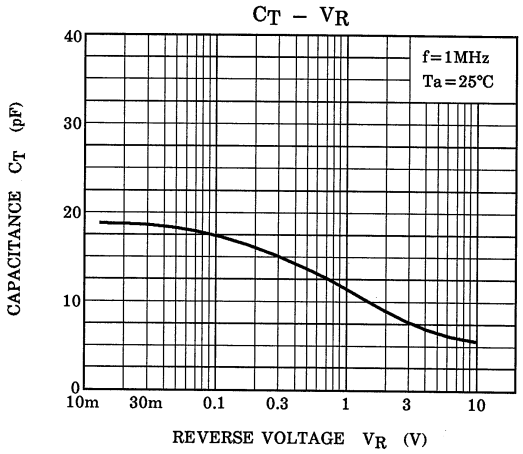
$P_D - Ta$



SBD Electrical Characteristics Graph







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